Subminiature Plastic Silicon Infrared Phototransistor

QSB363

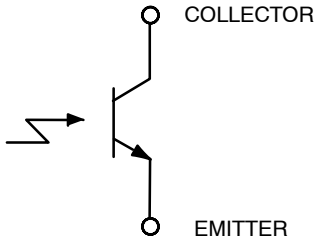
Description

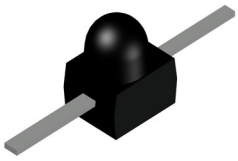
The QSB363 is a silicon phototransistor encapsulated in a black infrared transparent T−3/4 package.

Features

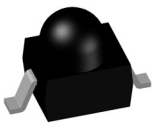
- NPN Silicon Phototransistor
- T−3/4 (2 mm) Surface Mount Package
- Medium Wide Beam Angle: 24°
- Black Plastic Package
- Matched Emitters: QEB363 or QEB373
- Daylight Filter
- Lead Form Options: Gullwing, Yoke, Z−Bend
- This is a Pb−Free Device and Halide Free Device

SCHEMATIC

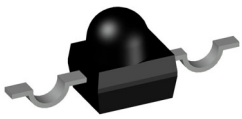




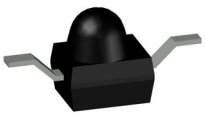
T−3/4 2.50 x 2.00
CASES 100CB



T−3/4 2.50 x 2.00
CASES 100EH



T−3/4 2.50 x 2.00
CASES 100EJ



T−3/4 2.50 x 2.00
CASES 100EK

ABSOLUTE MAXIMUM RATINGS (Values are at TA = 25°C unless specified otherwise).

Symbol	Parameter	Value	Unit
T_{OPR}	Operating Temperature	−40 to +85	°C
T_{STG}	Storage Temperature	−40 to +85	°C
T_{SOL-I}	Soldering Temperature (Iron) (Notes 1, 2)	260	°C
T_{SOL-F}	Soldering Temperature (Flow) (Notes 1, 2)	260	°C
V_{CEO}	Collector−Emitter Voltage	30	V
V_{ECO}	Emitter−Collector Voltage	5	V
P_C	Power Dissipation (Note 3)	75	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. RMA flux is recommended.
2. Methanol or isopropyl alcohols are recommended as cleaning agents.
3. Derate power dissipation linearly 1.08 mW/°C above 25°C.

ORDERING INFORMATION

Device	Package	Shipping†
QSB363	T−3/4 2.50 x 2.00 100CB (Pb-Free, Halide Free)	1000 / Bulk Bag
QSB363GR	T−3/4 2.50 x 2.00 100EH (Pb-Free, Halide Free)	1000 / Tape & Reel
QSB363YR	T−3/4 2.50 x 2.00 100EJ (Pb-Free, Halide Free)	1000 / Tape & Reel
QSB363ZR	T−3/4 2.50 x 2.00 100EK (Pb-Free, Halide Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL/OPTICAL CHARACTERISTICS (Values are at T_A = 25°C unless specified otherwise).

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
λ_P	Peak Sensitivity Wavelength		–	940	–	nm
Θ	Reception Angle		–	±12		°
I_{CEO}	Collector Dark Current	V_{CE} = 20 V, E_e = 0 mW/cm^2	–	–	100	nA
BV_{CEO}	Collector−Emitter Breakdown Voltage	I_C = 100 μA, E_e = 0 mW/cm^2	30	–	–	V
BV_{ECO}	Emitter−Collector Breakdown Voltage	I_E = 100 μA, E_e = 0 mW/cm^2	5	–	–	V
$I_{C(ON)}$	On−State Collector Current	V_{CE} = 5 V, E_e = 1 mW/cm^2, λ = 940 nm GaAs	1.0	1.5	–	mA
$V_{CE(SAT)}$	Collector−Emitter Saturation Voltage	I_C = 2 mA, E_e = 1 mW/cm^2, λ = 940 nm GaAs	–	–	0.4	V
t_r	Rise Time	V_{CE} = 5 V, I_C = 1 mA, RL = 1000 Ω	–	15	–	μs
t_f	Fall Time		–	15	–	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

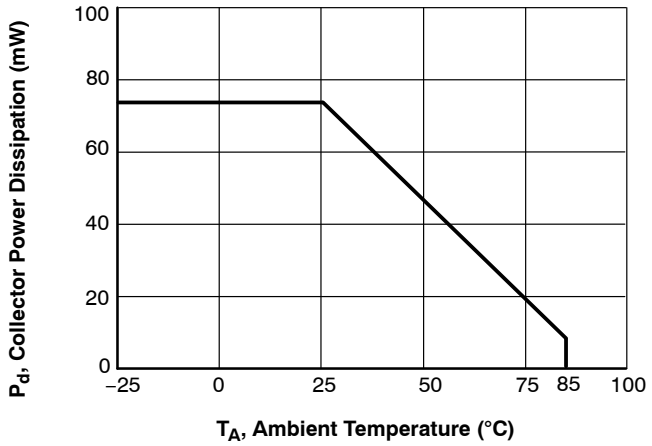


Figure 1. Collector Power Dissipation vs. Ambient Temperature

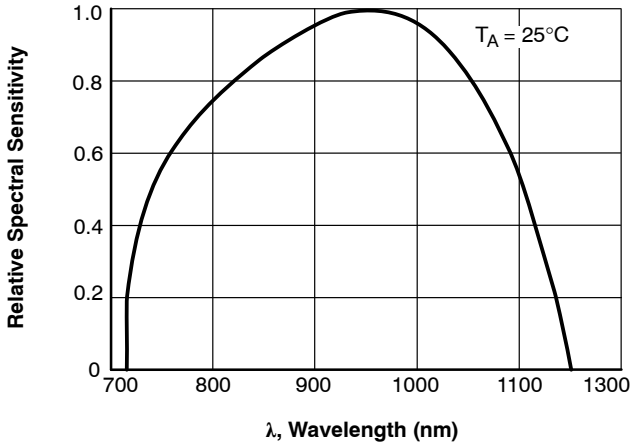


Figure 2. Spectral Sensitivity

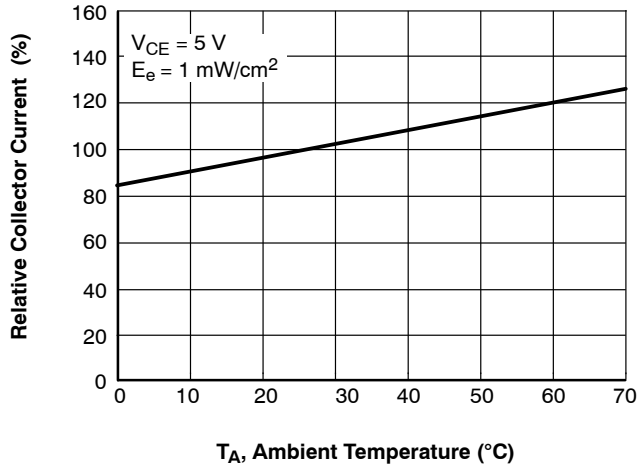


Figure 3. Relative Collector Current vs. Ambient Temperature

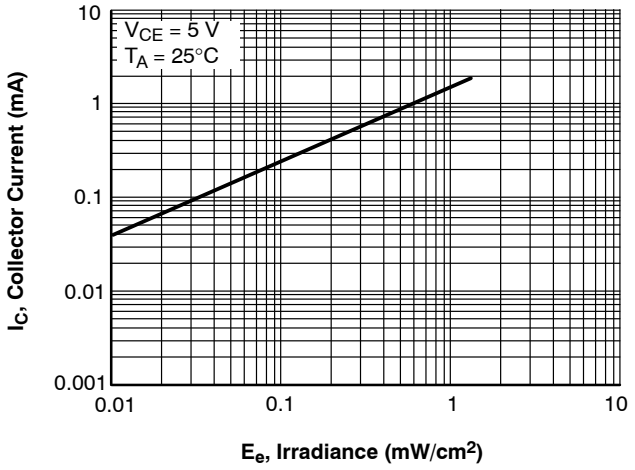


Figure 4. Collector Current vs. Irradiance

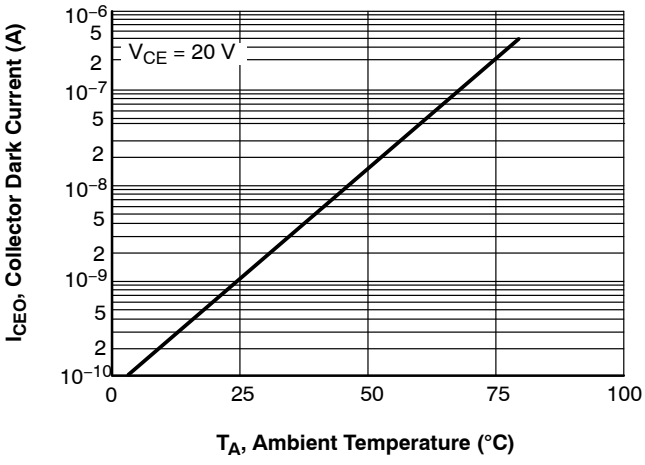


Figure 5. Collector Dark Current vs. Ambient Temperature

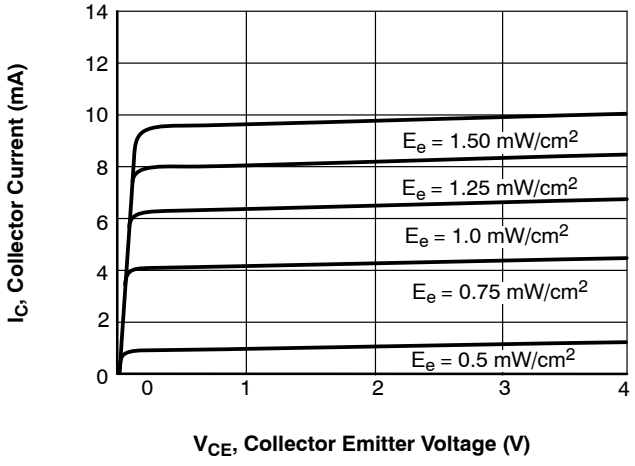
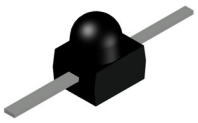


Figure 6. Collector Current vs. Collector Emitter Voltage

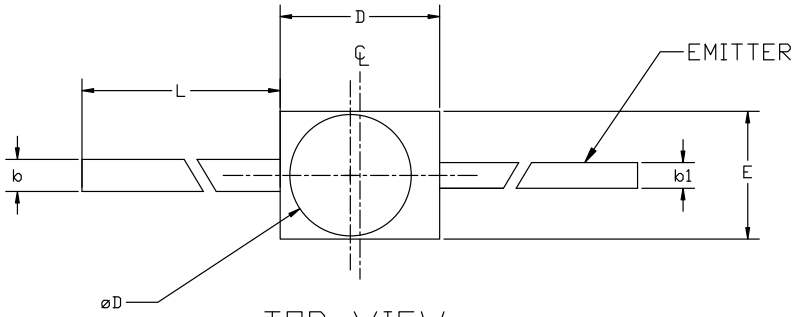


T−3/4 2.50x2.00
CASE 100CB
ISSUE A

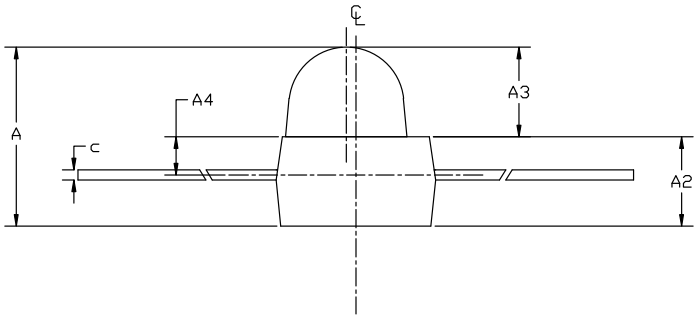
DATE 14 SEP 2023

NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
3. 2MM DETECTOR

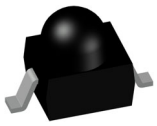


TOP VIEW



FRONT VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.50	2.70	2.90
A2	1.30	1.40	1.50
A3	1.30	1.40	1.50
A4		0.60 REF	
b	0.45	0.55	0.65
b1	0.35	0.45	0.55
c	0.10	0.15	0.25
D	2.30	2.50	2.70
E	1.80	2.00	2.20
L	7.00	---	---
øD	1.70	1.90	2.10

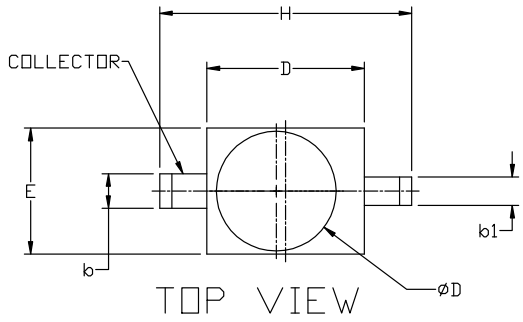


T−3/4 2.50x2.00
CASE 100EH
ISSUE O

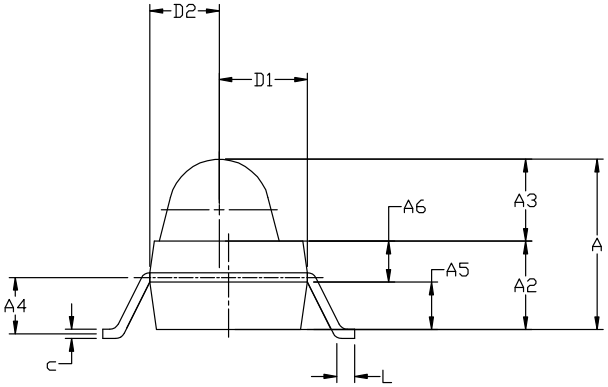
DATE 14 SEP 2023

NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
3. 2MM GULLWING DETECTOR.

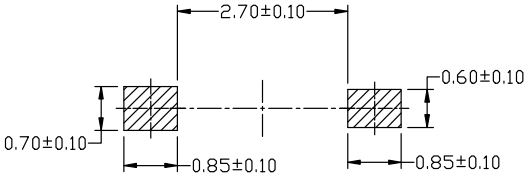


TOP VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.500	2.700	2.900
A2	1.300	1.400	1.500
A3	1.200	1.300	1.400
A4	0.750	0.850	0.950
A5	0.650	0.750	0.850
A6	0.550	0.650	0.750
b	0.450	0.550	0.650
b1	0.350	0.450	0.550
c	0.100	0.150	0.200
D	2.300	2.500	2.700
D1	1.200	1.400	1.600
D2	0.900	1.100	1.300
E	1.800	2.000	2.200
H	3.800	4.000	4.200
L	0.200	0.300	0.400
øD	1.700	1.900	2.100
R1	0.700	0.800	0.900



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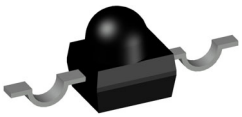


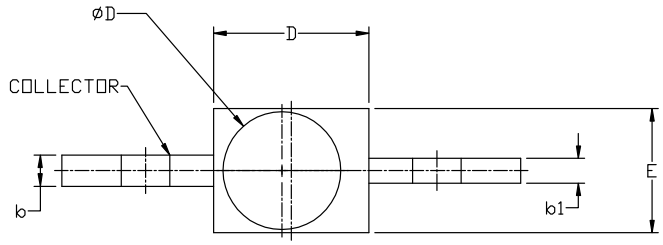
T−3/4 2.50x2.00
CASE 100EJ
ISSUE O

DATE 14 SEP 2023

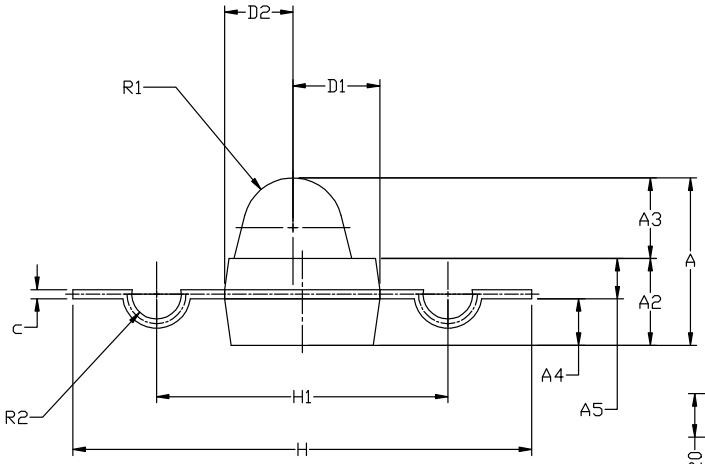
NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
3. 2MM YOKE DETECTOR.

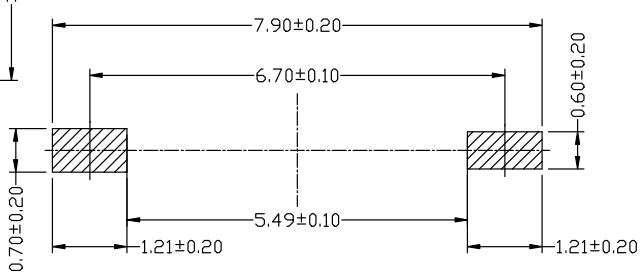
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.500	2.700	2.900
A2	1.300	1.400	1.500
A3	1.200	1.300	1.400
A4	0.650	0.750	0.850
A5	0.550	0.650	0.750
b	0.450	0.550	0.650
b1	0.350	0.450	0.550
c	0.100	0.150	0.200
D	2.300	2.500	2.700
D1	1.200	1.400	1.600
D2	0.900	1.100	1.300
E	1.800	2.000	2.200
H	7.200	7.400	7.600
H1	4.500	4.700	4.900
ØD	1.700	1.900	2.100
R1	0.700	0.800	0.900
R2	0.300	0.400	0.500



TOP VIEW



BOTTOM VIEW



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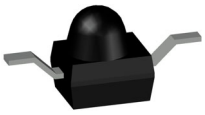

T−3/4 2.50x2.00
CASE 100EK
ISSUE O

DATE 14 SEP 2023

NOTES:

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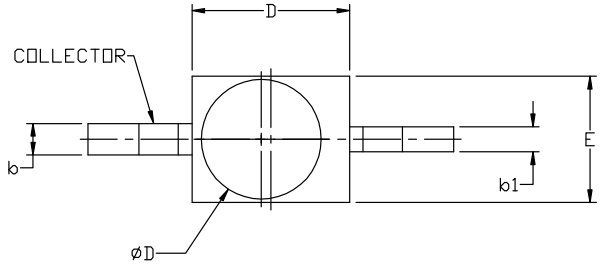
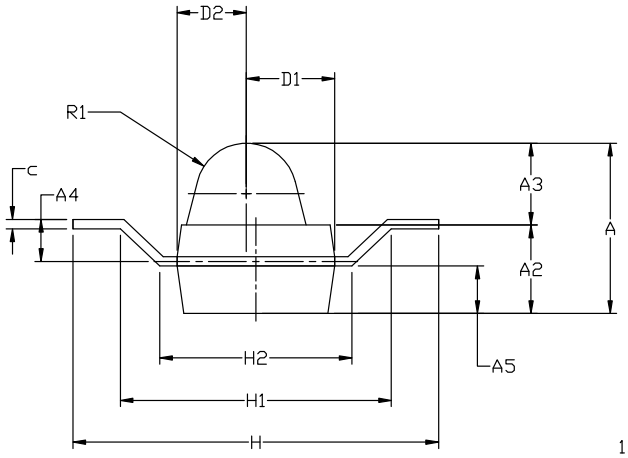
2. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
3. 2MM ZBEND DETECTOR.

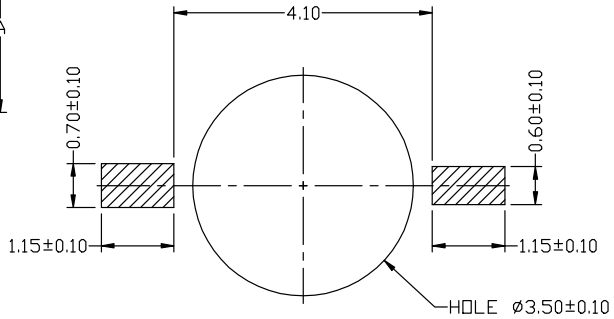


TOP VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.500	2.700	2.900
A2	1.300	1.400	1.500
A3	1.200	1.300	1.400
A4	0.550	0.650	0.750
A5	0.650	0.750	0.850
b	0.450	0.550	0.650
b1	0.350	0.450	0.550
c	0.100	0.150	0.200
D	2.300	2.500	2.700
D1	1.200	1.400	1.600
D2	0.900	1.100	1.300
E	1.800	2.000	2.200
H	5.600	5.800	6.000
H1	4.100	4.300	4.500
H2	2.850	3.050	3.250
øD	1.700	1.900	2.100
R1	0.700	0.800	0.900



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